



STB13NM50N/-1 - STF13NM50N STP13NM50N - STW13NM50N

N-channel 500V - 0.250Ω - 12A - TO-220/FP - TO-247-I²/D²PAK
Second generation MDmesh™ Power MOSFET

Features

Type	V _{DSS} (@T _{Jmax})	R _{DS(on)}	I _D
STB13NM50N	550V	<0.32Ω	12A
STB13NM50N-1	550V	<0.32Ω	12A
STF13NM50N	550V	<0.32Ω	12A ⁽¹⁾
STP13NM50N	550V	<0.32Ω	12A
STW13NM50N	550V	<0.32Ω	12A

1. Limited only by maximum temperature allowed

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Description

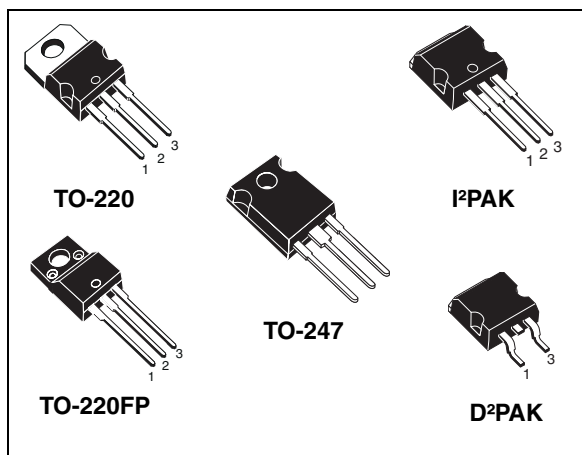
This product is realized with the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters

Application

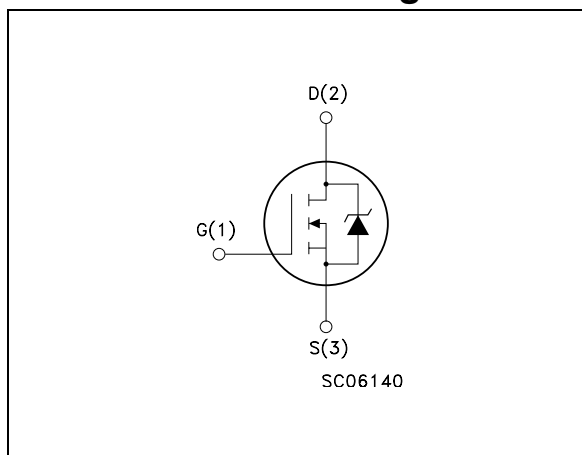
- Switching application

Order codes

Part number	Marking	Package	Packaging
STB13NM50N-1	B13NM50N	I ² PAK	Tube
STB13NM50N	B13NM50N	D ² PAK	Tape & reel
STP13NM50N	P13NM50N	TO-220	Tube
STF13NM50N	F13NM50N	TO-220FP	Tube
STW13NM50N	W13NM50N	TO-247	Tube



Internal schematic diagram



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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220/TO-247 D ² PAK/I ² PAK	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS}=0$)	500		V
V_{GS}	Gate-source voltage	± 25		V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	12	12 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	6	6 ⁽¹⁾	A
$I_{DM}^{(2)}$	Drain current (pulsed)	48	48 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	100	25	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{s}; T_C=25^\circ\text{C}$)	--	2500	V
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 150		$^\circ\text{C}$

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 12\text{A}$, $di/dt \leq 400\text{A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		TO-220/TO-247 D ² PAK/I ² PAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	1.25	5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-amb max	62.5		$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300		$^\circ\text{C}$

Table 3. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	3.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25^\circ\text{C}$, $I_D=I_{AS}$, $V_{DD}=50\text{V}$)	200	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{mA}$, $V_{GS} = 0$	500			V
$dv/dt^{(1)}$	Drain-source voltage slope	$V_{DD}=400\text{V}$, $I_D=12\text{A}$, $V_{GS}=10\text{V}$	30			V/ns
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating}$, $T_c=125^{\circ}\text{C}$			1 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 6\text{A}$		0.25	0.32	Ω

1. Characteristics value at turn off on inductive load

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}$, $I_D = 6\text{A}$		8		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50\text{V}$, $f=1\text{MHz}$, $V_{GS}=0$		960 50 5		pF pF pF
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS}=0$, $V_{DS}=0\text{V to } 480\text{V}$		110		pF
R_g	Gate input resistance	$f=1\text{MHz}$ Gate DC Bias=0 test signal level=20mV open drain		5		Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD}=400\text{V}$, $I_D = 12\text{A}$ $V_{GS}=10\text{V}$ (see Figure 18)		30 5 15		nC nC nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=250V$, $I_D=6A$, $R_G=4.7\Omega$, $V_{GS}=10V$ (see Figure 17)		30		ns
t_r	Rise time			15		ns
$t_{d(off)}$	Turn-off delay time			40		ns
t_f	Fall time			10		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				12	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				48	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=12A$, $V_{GS}=0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD}=12A$, $V_{DD}=100V$ $di/dt = 100A/\mu s$, $T_j=25^\circ C$ (see Figure 19)		300		ns
Q_{rr}	Reverse recovery charge			3		μC
I_{RRM}	Reverse recovery current			22		A
t_{rr}	Reverse recovery time	$I_{SD}=12A$, $V_{DD}=100V$ $di/dt=100A/\mu s$, $T_j=150^\circ C$ (see Figure 19)		370		ns
Q_{rr}	Reverse recovery charge			4		μC
I_{RRM}	Reverse recovery current			22		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220 / D²PAK / I²PAK

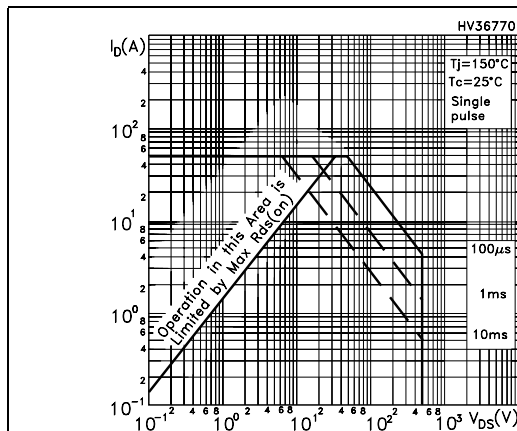


Figure 2. Thermal impedance for TO-220 / D²PAK / I²PAK

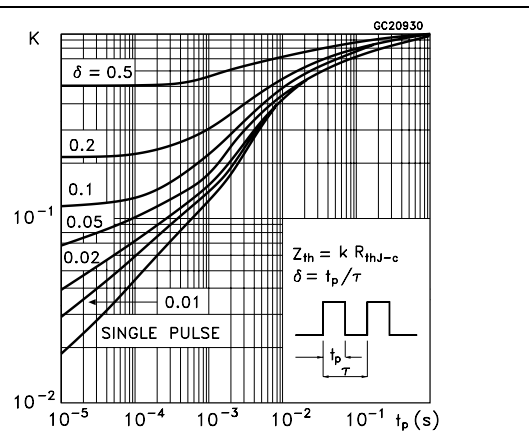


Figure 3. Safe operating area for TO-220FP

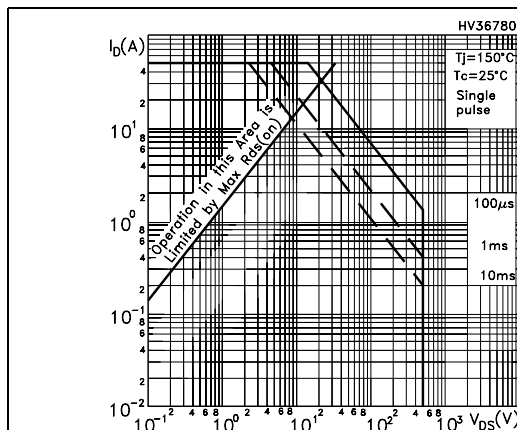


Figure 4. Thermal impedance for TO-220FP

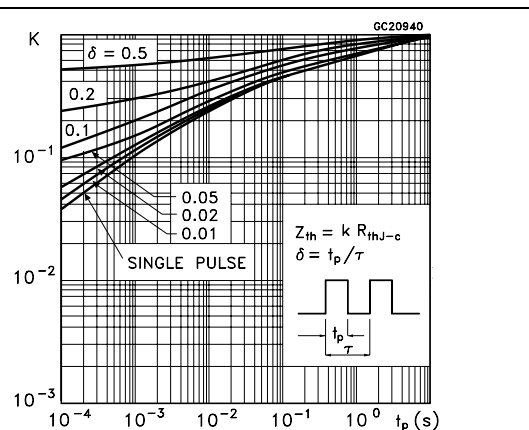


Figure 5. Safe operating area for TO-247

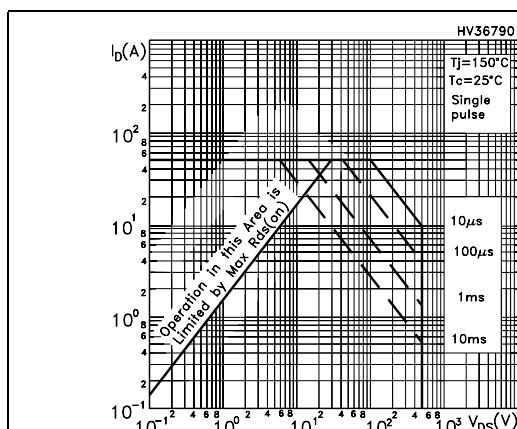


Figure 6. Thermal impedance for TO-247

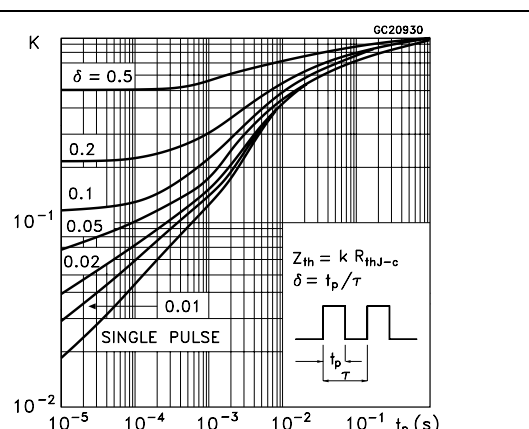


Figure 7. Output characteristics

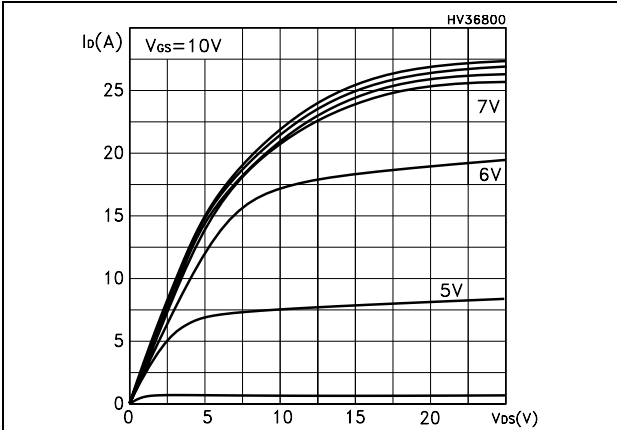


Figure 8. Transfer characteristics

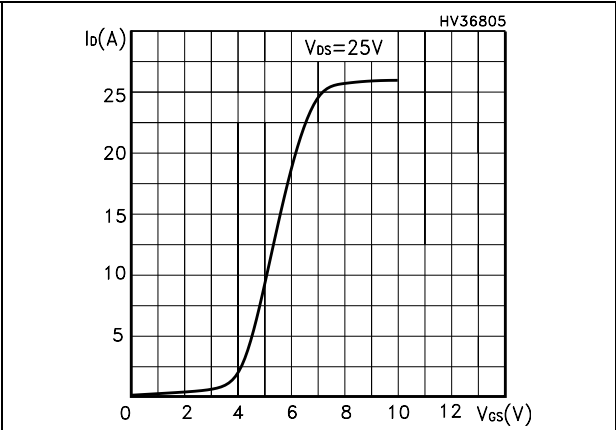


Figure 9. Transconductance

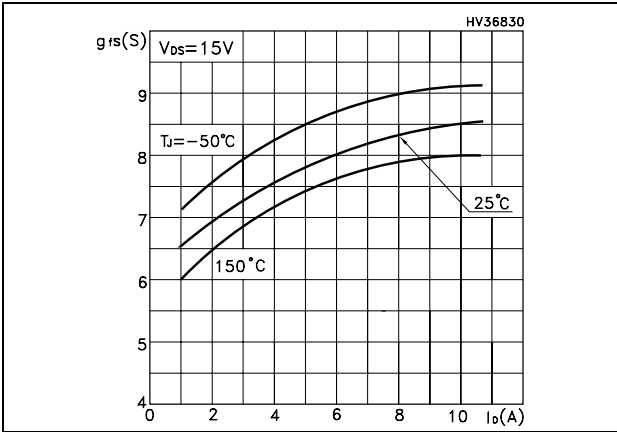


Figure 10. Static drain-source on resistance

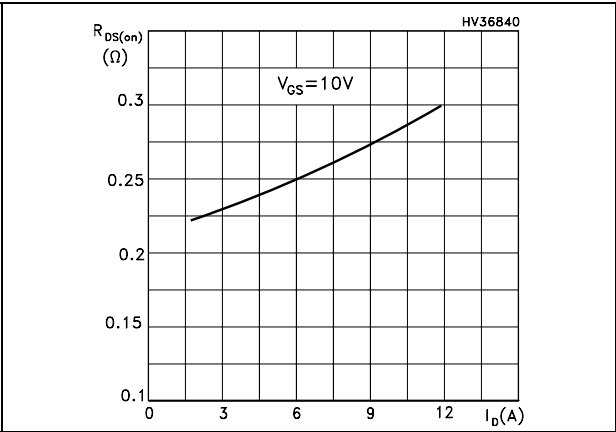


Figure 11. Gate charge vs gate-source voltage

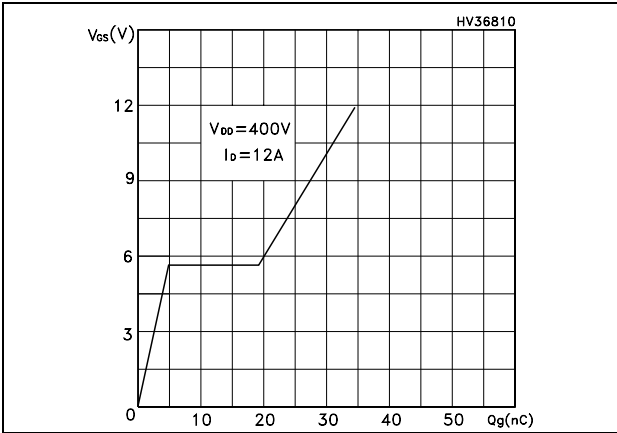


Figure 12. Capacitance variations

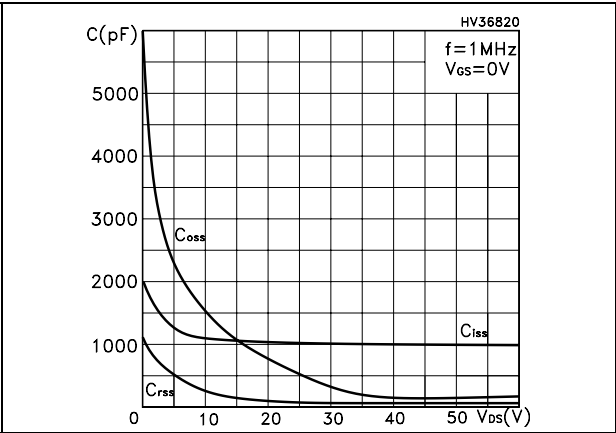


Figure 13. Normalized gate threshold voltage vs temperature

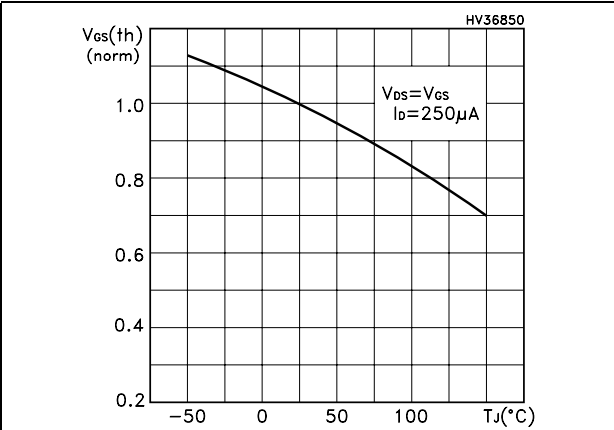


Figure 14. Normalized on resistance vs temperature

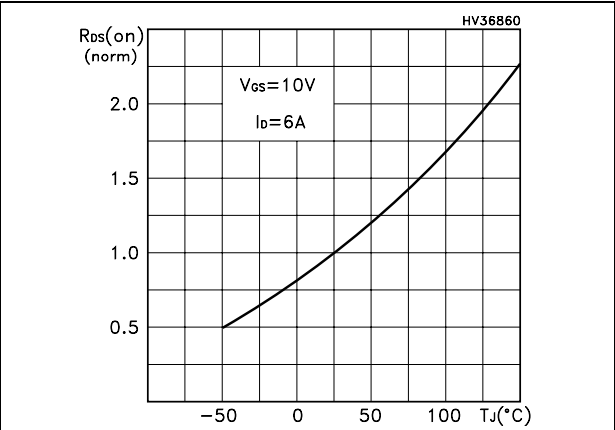


Figure 15. Source-drain diode forward characteristics

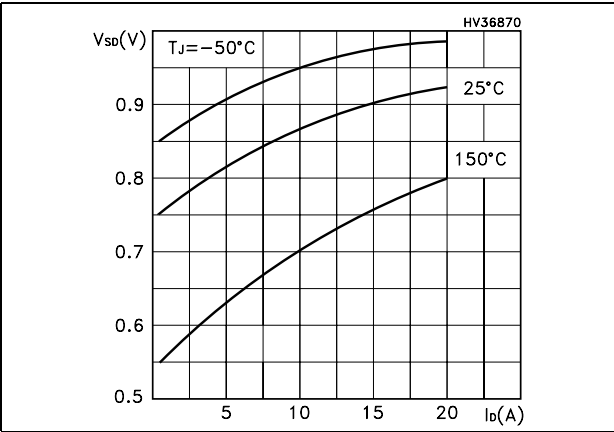
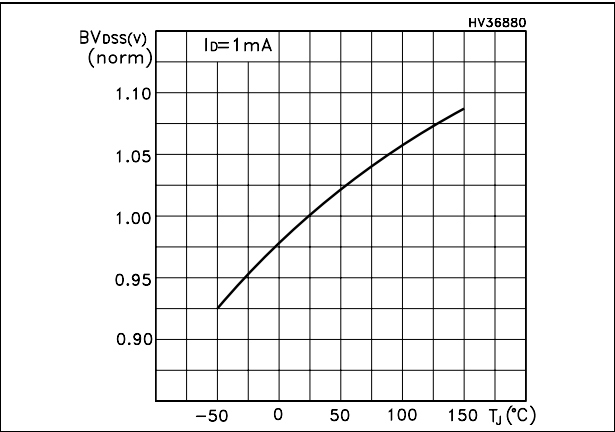


Figure 16. Normalized BVdss vs temperature



3 Test circuit

Figure 17. Switching times test circuit for resistive load

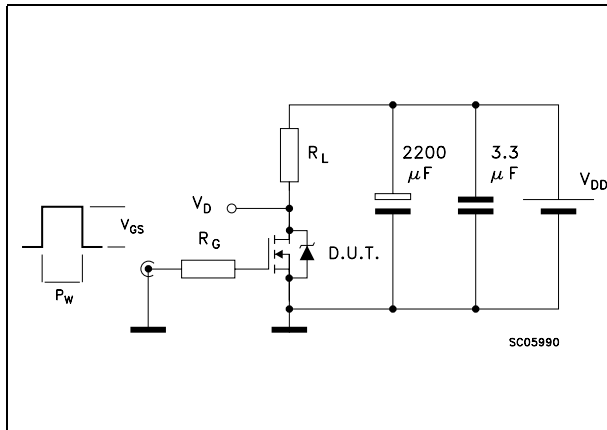


Figure 18. Gate charge test circuit

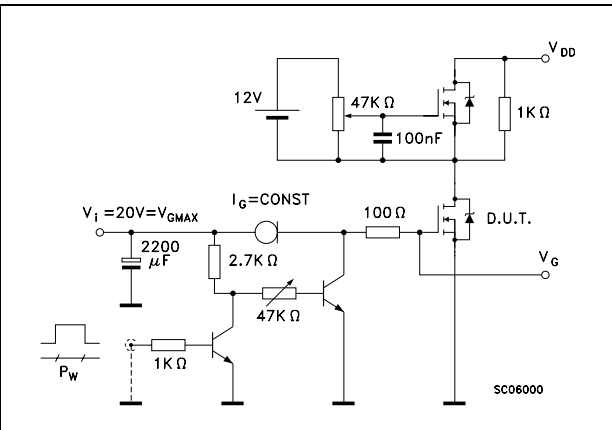


Figure 19. Test circuit for inductive load switching and diode recovery times

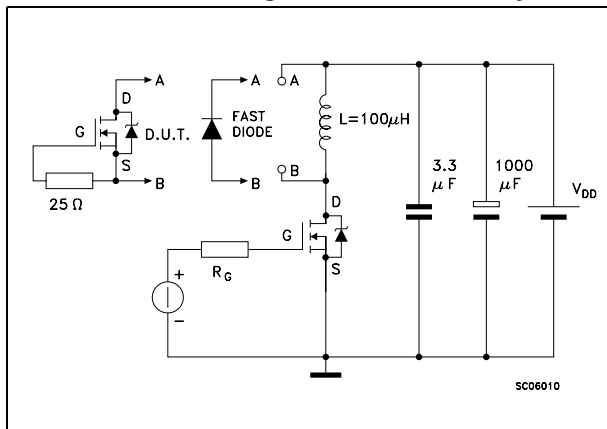


Figure 20. Unclamped inductive load test circuit

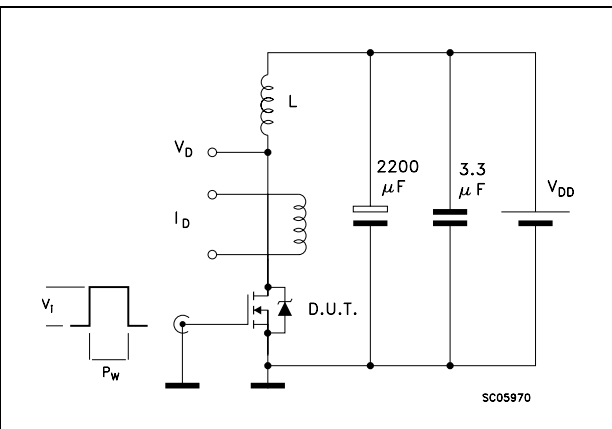


Figure 21. Unclamped inductive waveform

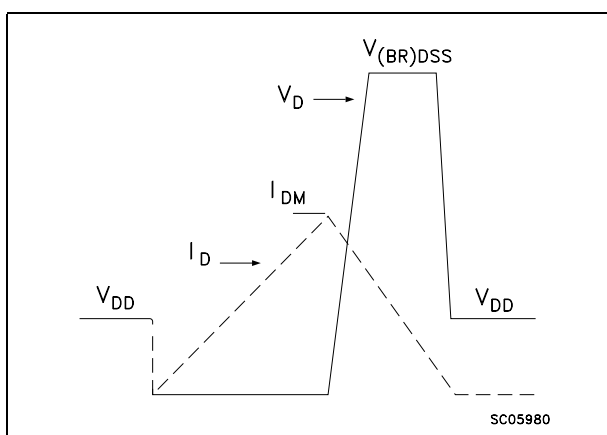
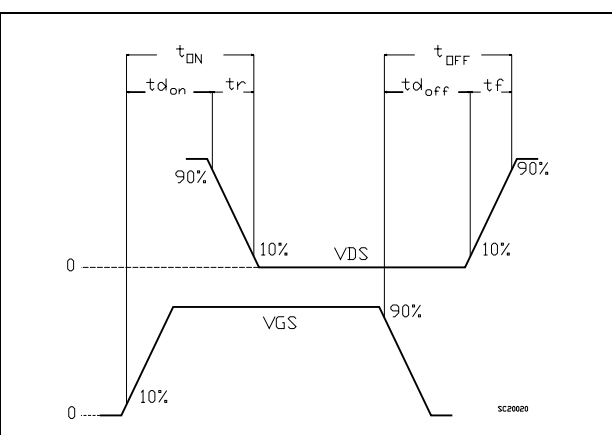


Figure 22. Switching time waveform

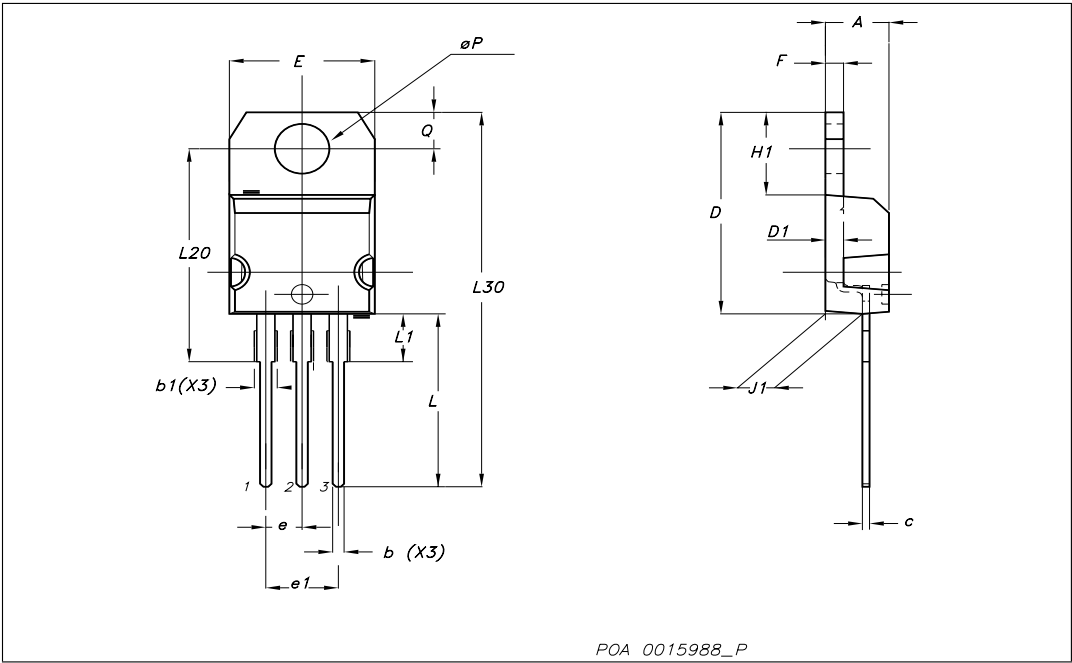


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 mechanical data

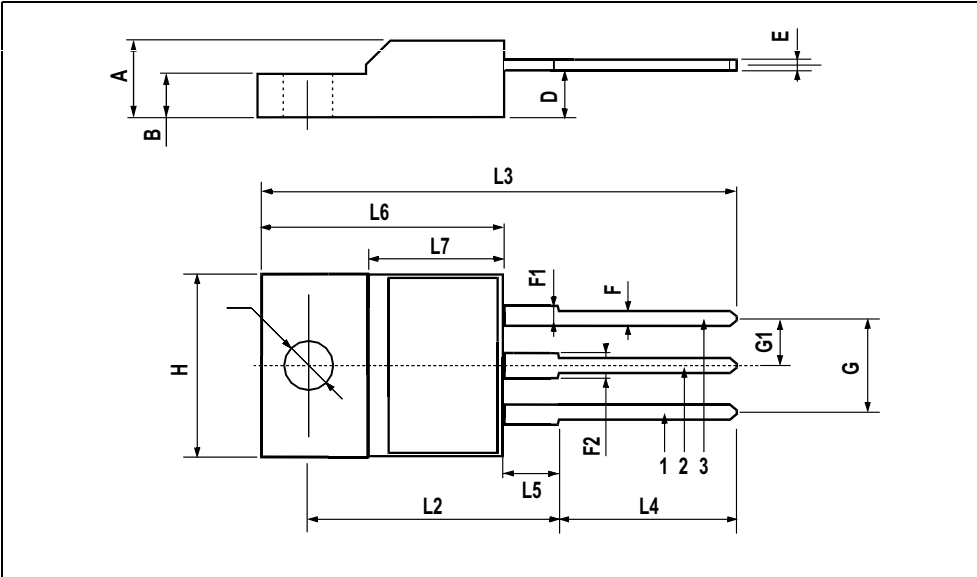
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



POA 0015988_P

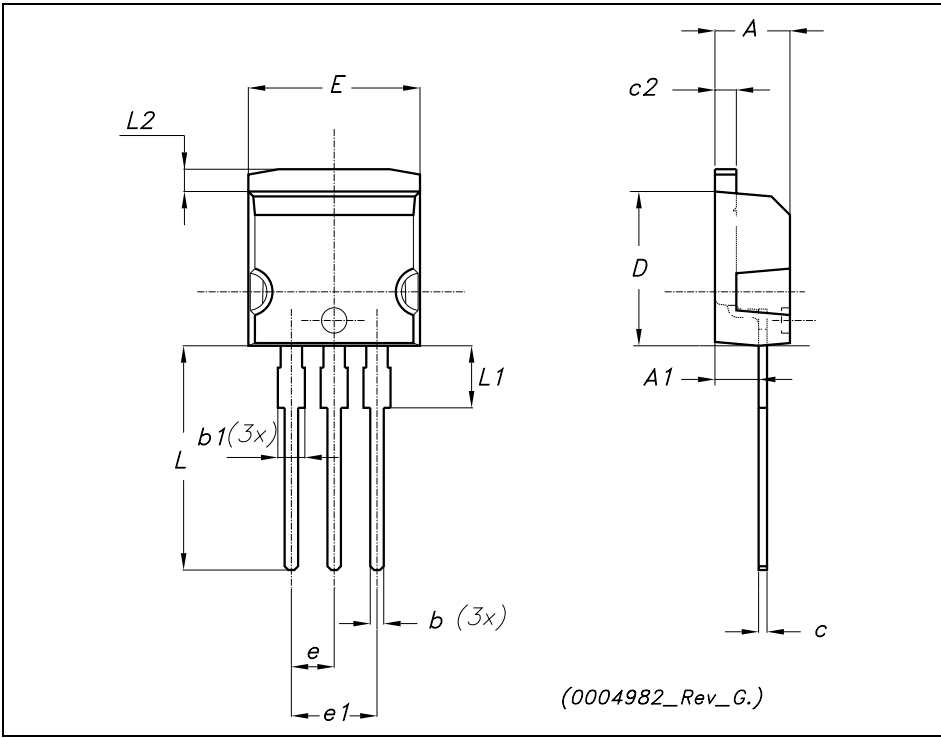
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



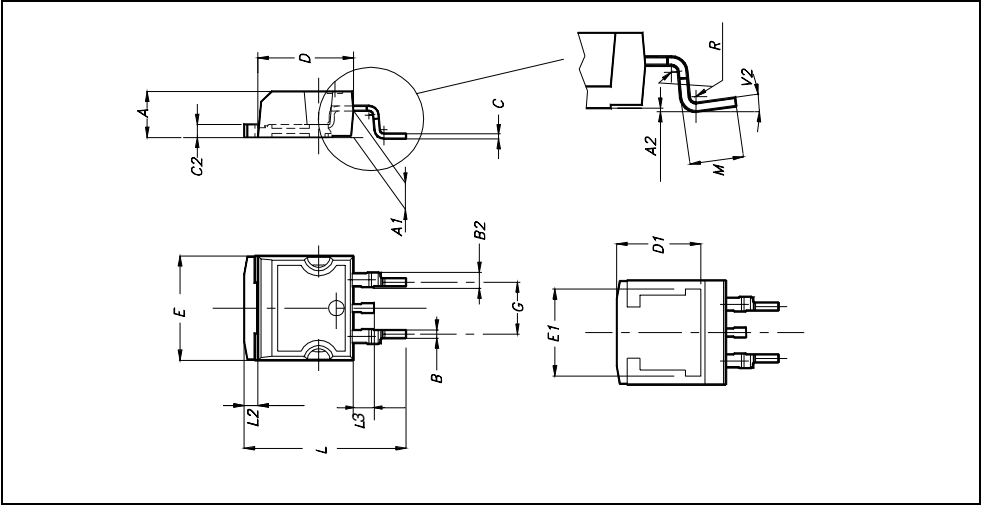
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



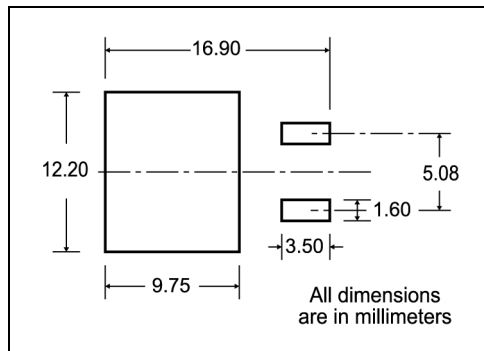
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

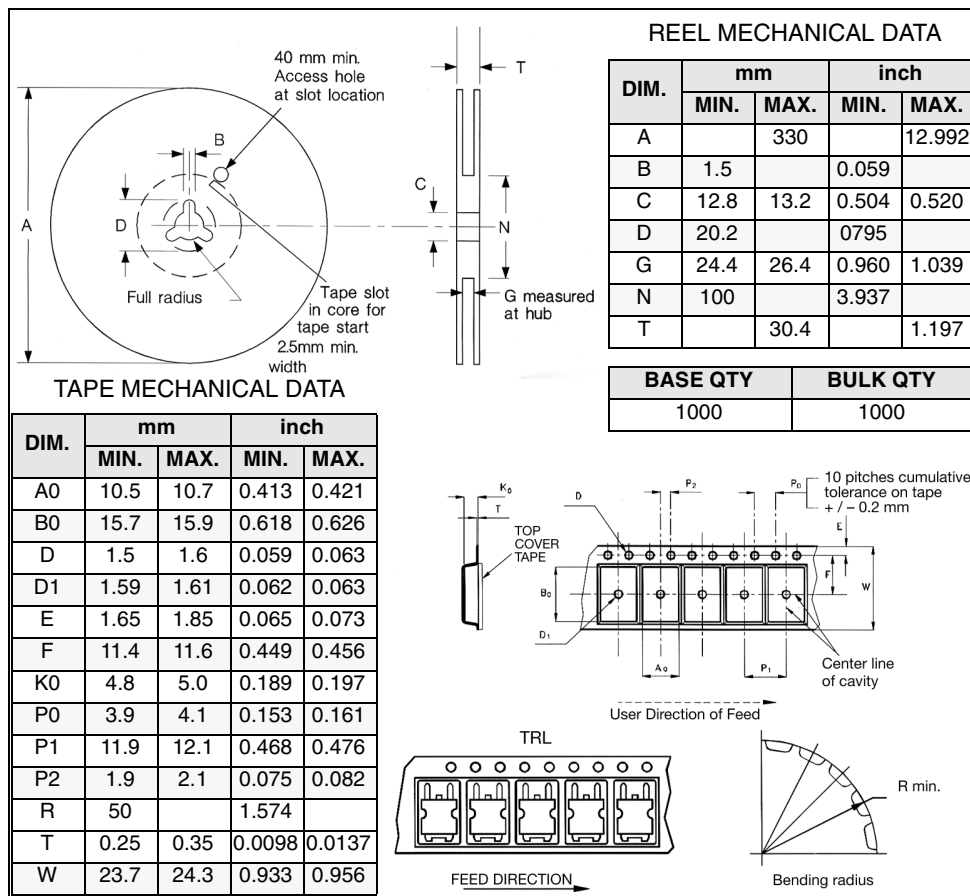


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes
18-Dec-2006	1	First release
08-May-2007	2	Added TO-247

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